

< HVIGBT MODULES >

CM750HG-130R

HIGH POWER SWITCHING USE
INSULATED TYPE

4th-Version HVIGBT (High Voltage Insulated Gate Bipolar Transistor) Modules

CM750HG-130R



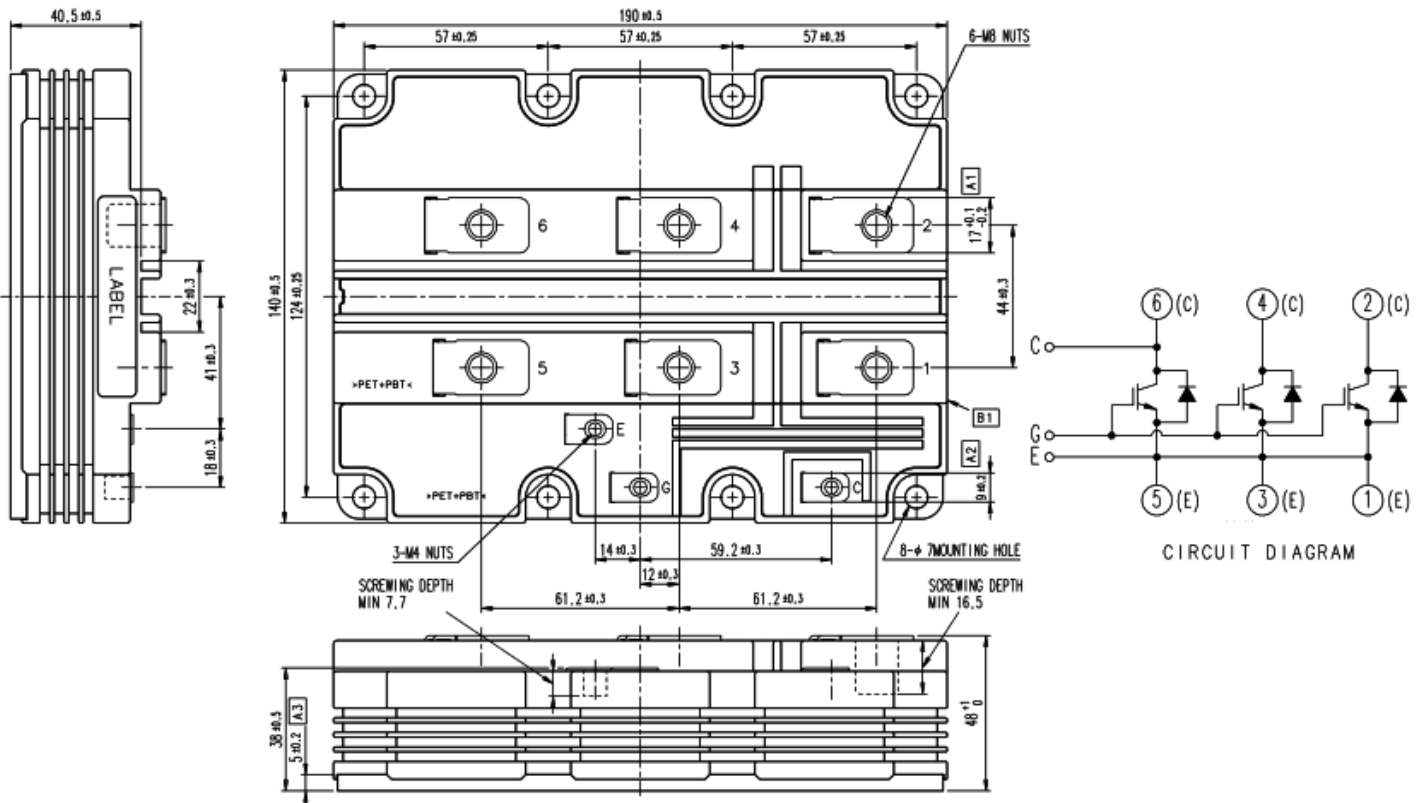
- I_C 750A
- V_{CES} 6500V
- 1-element in a Pack
- High insulated Type
- LPT-IGBT / Soft Recovery Diode
- AISiC Baseplate

APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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MAXIMUM RATINGS

Symbol	Item	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	V _{GE} = 0V, T _j = +125 °C	6500	V
		V _{GE} = 0V, T _j = +25°C	6300	
		V _{GE} = 0V, T _j = -50°C	5700	
V _{GES}	Gate-emitter voltage	V _{CE} = 0V, T _j = 25°C	±20	V
I _C	Collector current	DC, T _c = 95°C	750	A
I _{CRM}		Pulse (Note 1)	1500	A
I _E	Emitter current (Note 2)	DC	750	A
I _{ERM}		Pulse (Note 1)	1500	A
P _{tot}	Maximum power dissipation (Note 3)	T _c = 25°C, IGBT part	10400	W
V _{iso}	Isolation voltage	RMS, sinusoidal, f = 60Hz, t = 1min.	10200	V
V _e	Partial discharge extinction voltage	RMS, sinusoidal, f = 60Hz, Q _{PD} ≤ 10 pC	5100	V
T _j	Junction temperature		-50 ~ +150	°C
T _{jop}	Operating junction temperature		-50 ~ +125	°C
T _{stg}	Storage temperature		-55 ~ +125	°C
t _{psc}	Short circuit pulse width	V _{CC} = 4500 V, V _{CE} ≤ V _{CES} , V _{GE} = 15V, T _j = 125°C	10	μs

ELECTRICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min	Typ	Max		
I _{CES}	Collector cutoff current	V _{CE} = V _{CES} , V _{GE} = 0V	T _j = 25°C	—	—	24.0	mA
			T _j = 125°C	—	24.0	—	
V _{GE(th)}	Gate-emitter threshold voltage	V _{CE} = 10V, I _C = 75mA, T _j = 25°C	5.8	6.3	6.8	V	
I _{GES}	Gate leakage current	V _{GE} = V _{GES} , V _{CE} = 0V, T _j = 25°C	-0.5	—	0.5	μA	
C _{ies}	Input capacitance	V _{CE} = 10V, V _{GE} = 0V, f = 100kHz T _j = 25°C	—	136.0	—	nF	
C _{oes}	Output capacitance		—	8.6	—	nF	
C _{res}	Reverse transfer capacitance		—	4.0	—	nF	
Q _G	Total gate charge	V _{CC} = 3600V, I _C = 750A, V _{GE} = ±15V	—	10.5	—	μC	
V _{CEsat}	Collector-emitter saturation voltage	I _C = 750A (Note 4) V _{GE} = 15V	T _j = 25°C	—	3.90	—	V
			T _j = 125°C	—	4.80	5.60	
t _{d(on)}	Turn-on delay time	V _{CC} = 3600V I _C = 750A V _{GE} = ±15V	T _j = 25°C	—	1.20	—	μs
			T _j = 125°C	—	1.15	1.80	
t _r	Turn-on rise time	R _{G(on)} = 3.9Ω L _s = 150nH	T _j = 25°C	—	0.20	—	μs
			T _j = 125°C	—	0.22	0.50	
E _{on(10%)}	Turn-on switching energy (Note 5)	Inductive load	T _j = 25°C	—	3.50	—	J
			T _j = 125°C	—	4.10	—	
E _{on}	Turn-on switching energy (Note 6)	Inductive load	T _j = 25°C	—	3.85	—	J
			T _j = 125°C	—	4.80	—	
t _{d(off)}	Turn-off delay time	V _{CC} = 3600V I _C = 750A V _{GE} = ±15V	T _j = 25°C	—	7.30	—	μs
			T _j = 125°C	—	7.80	9.00	
t _f	Turn-off fall time	R _{G(off)} = 33Ω L _s = 150nH	T _j = 25°C	—	0.36	—	μs
			T _j = 125°C	—	0.44	1.00	
E _{off(10%)}	Turn-off switching energy (Note 5)	Inductive load	T _j = 25°C	—	3.40	—	J
			T _j = 125°C	—	4.60	—	
E _{off}	Turn-off switching energy (Note 6)	Inductive load	T _j = 25°C	—	3.60	—	J
			T _j = 125°C	—	4.90	—	

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INSULATED TYPE

4th-Version HVIGBT (High Voltage Insulated Gate Bipolar Transistor) Modules

ELECTRICAL CHARACTERISTICS (continuation)

Symbol	Item	Conditions	Limits			Unit	
			Min	Typ	Max		
V _{EC}	Emitter-collector voltage (Note 2)	I _E = 750A V _{GE} = 0V (Note 4)	T _J = 25°C	—	3.00	—	V
			T _J = 125°C	—	3.20	3.80	
t _{rr}	Reverse recovery time (Note 2)	V _{CC} = 3600V I _C = 750A V _{GE} = ±15V R _{G(on)} = 3.9Ω L _s = 150nH Inductive load	T _J = 25°C	—	0.55	—	μs
			T _J = 125°C	—	0.75	—	
I _{rr}	Reverse recovery current (Note 2)	V _{CC} = 3600V I _C = 750A V _{GE} = ±15V R _{G(on)} = 3.9Ω L _s = 150nH Inductive load	T _J = 25°C	—	900	—	A
			T _J = 125°C	—	1000	—	
Q _{rr}	Reverse recovery charge (Note 2)	V _{CC} = 3600V I _C = 750A V _{GE} = ±15V R _{G(on)} = 3.9Ω L _s = 150nH Inductive load	T _J = 25°C	—	750	—	μC
			T _J = 125°C	—	1100	—	
E _{rec(10%)}	Reverse recovery energy (Note 2)(Note 5)	V _{CC} = 3600V I _C = 750A V _{GE} = ±15V R _{G(on)} = 3.9Ω L _s = 150nH Inductive load	T _J = 25°C	—	1.05	—	J
			T _J = 125°C	—	1.85	—	
E _{rec}	Reverse recovery energy (Note 2)(Note 6)	V _{CC} = 3600V I _C = 750A V _{GE} = ±15V R _{G(on)} = 3.9Ω L _s = 150nH Inductive load	T _J = 25°C	—	1.40	—	J
			T _J = 125°C	—	2.10	—	

THERMAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
R _{th(j-c)Q}	Thermal resistance	Junction to Case, IGBT part	—	—	12.0	K/kW
R _{th(j-c)D}		Junction to Case, FWDi part	—	—	22.0	
R _{th(c-s)}	Contact thermal resistance	Case to heat sink, λ _{grease} = 1W/m ² ·k, D _(c-s) = 100μm	—	6.0	—	K/kW

MECHANICAL CHARACTERISTICS

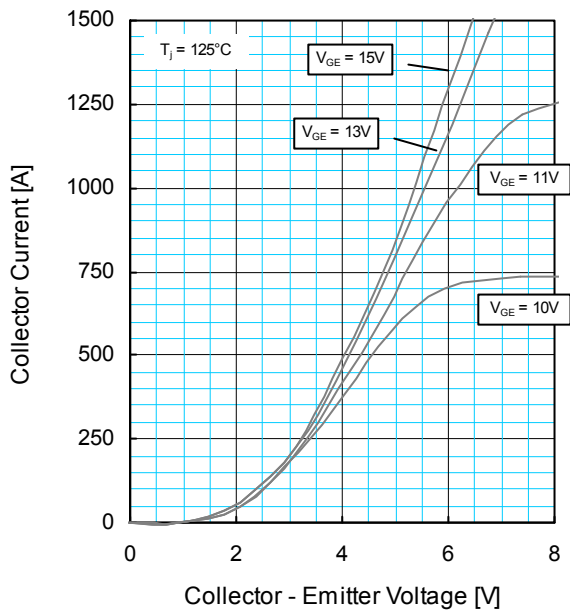
Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
M _t	Mounting torque	M : Main terminals screw	7.0	—	22.0	N·m
M _s		M : Mounting screw	3.0	—	6.0	N·m
M _t		M : Auxiliary terminals screw	1.0	—	3.0	N·m
m	Mass		—	1.4	—	kg
CTI	Comparative tracking index		600	—	—	—
d _a	Clearance		26.0	—	—	mm
d _s	Creepage distance		56.0	—	—	mm
L _{P CE}	Parasitic stray inductance		—	15.0	—	nH
R _{CC+EE'}	Internal lead resistance	T _c = 25°C	—	0.18	—	mΩ
r _g	Internal gate resistance	T _c = 25°C	—	2.6	—	Ω

Note1. Pulse width and repetition rate should be such that junction temperature (T_J) does not exceed Topmax rating.

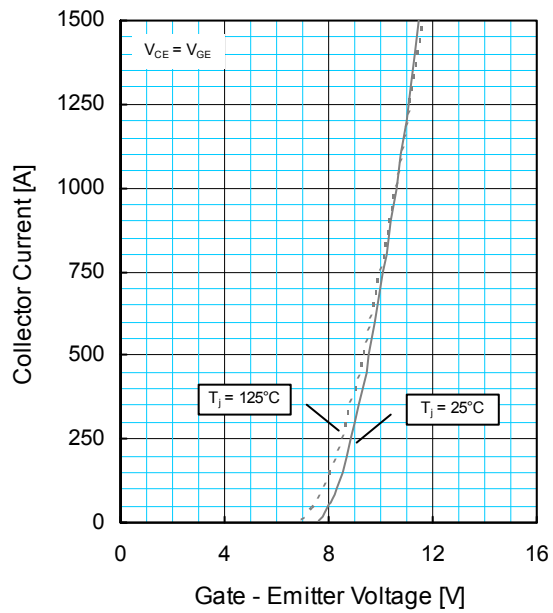
- The symbols represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWD).
- Junction temperature (T_J) should not exceed T_{Jmax} rating (150°C).
- Pulse width and repetition rate should be such as to cause negligible temperature rise.
- E_{on(10%)} / E_{off(10%)} / E_{rec(10%)} are the integral of 0.1V_{CE} × 0.1I_C × dt.
- Definition of all items is according to IEC 60747, unless otherwise specified.

PERFORMANCE CURVES

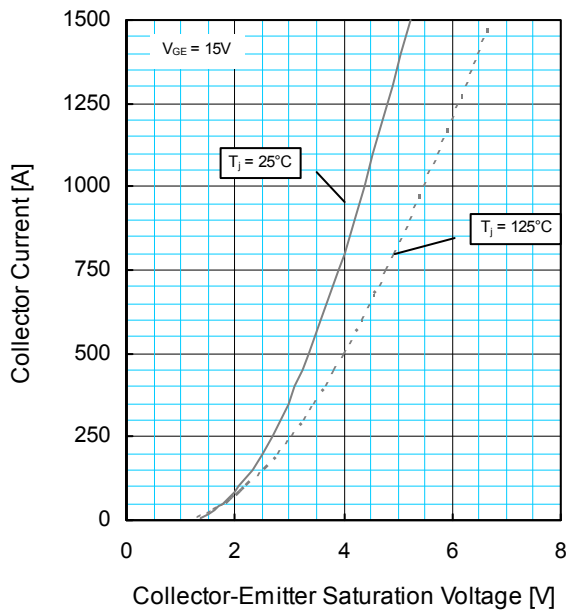
OUTPUT CHARACTERISTICS (TYPICAL)



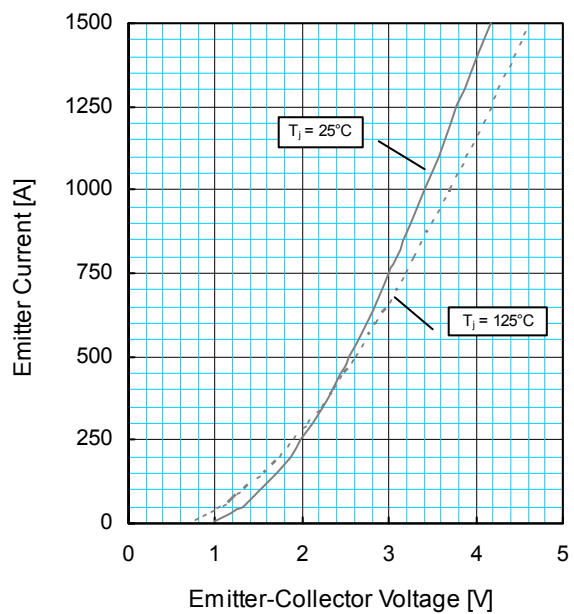
TRANSFER CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

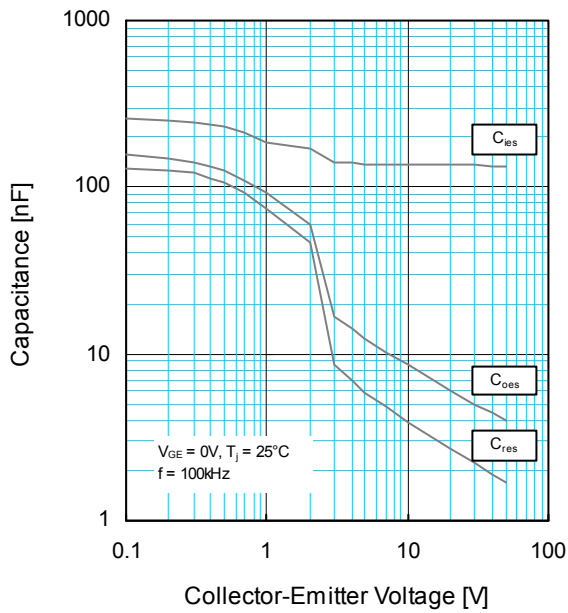


FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)

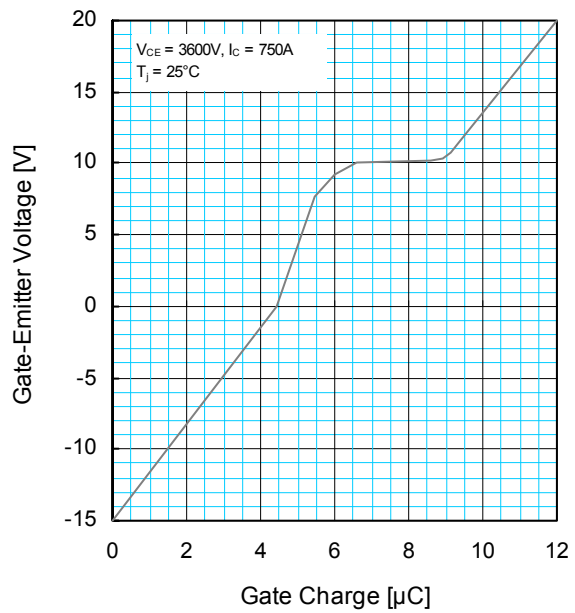


PERFORMANCE CURVES

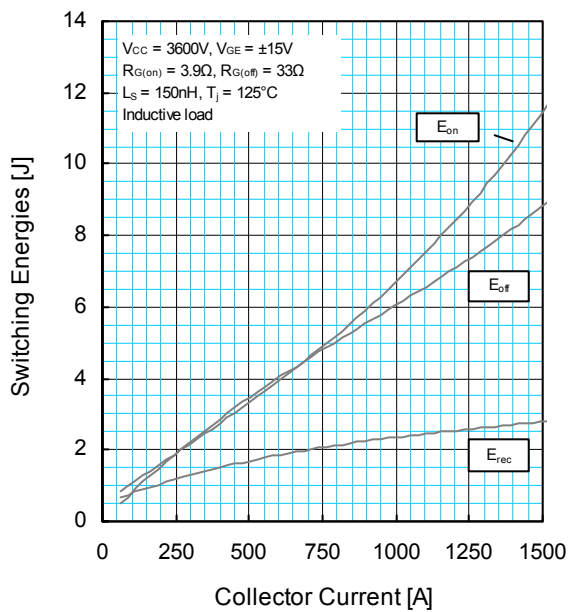
CAPACITANCE CHARACTERISTICS (TYPICAL)



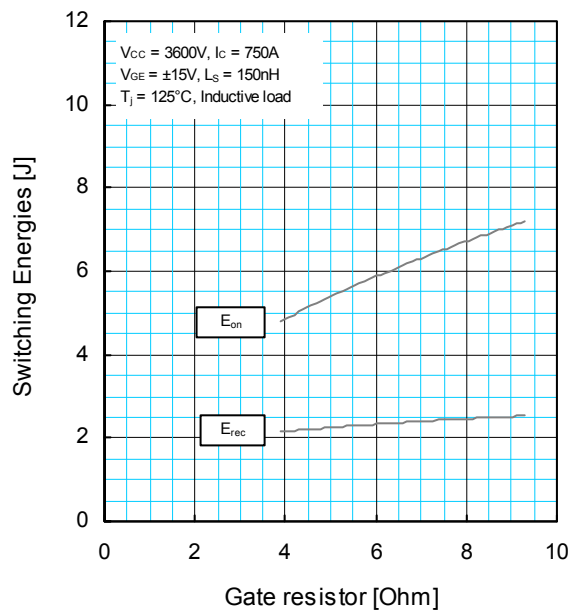
GATE CHARGE CHARACTERISTICS (TYPICAL)



HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)

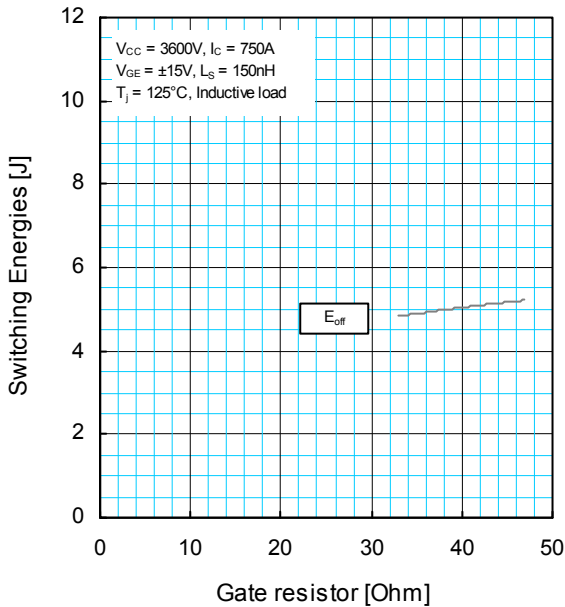


HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)

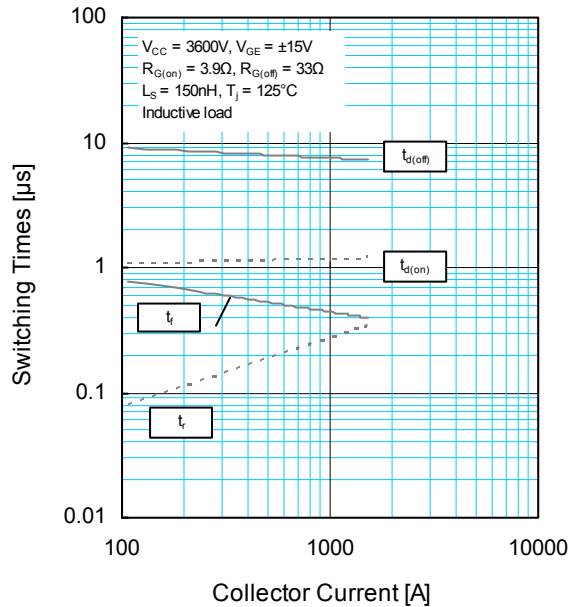


PERFORMANCE CURVES

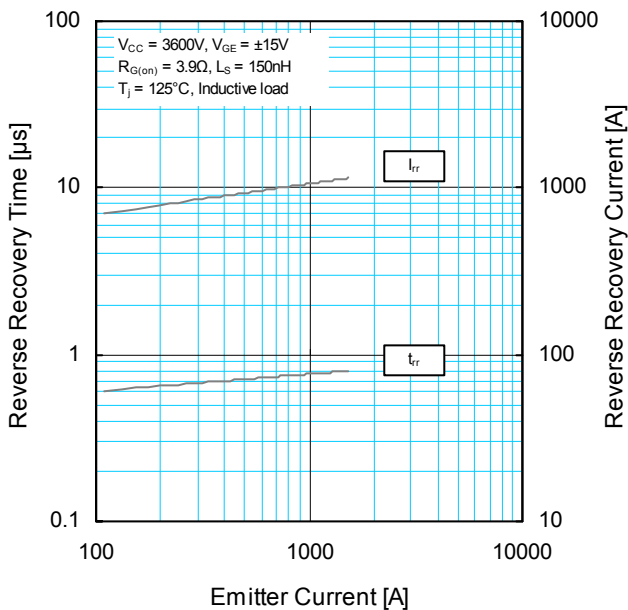
HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



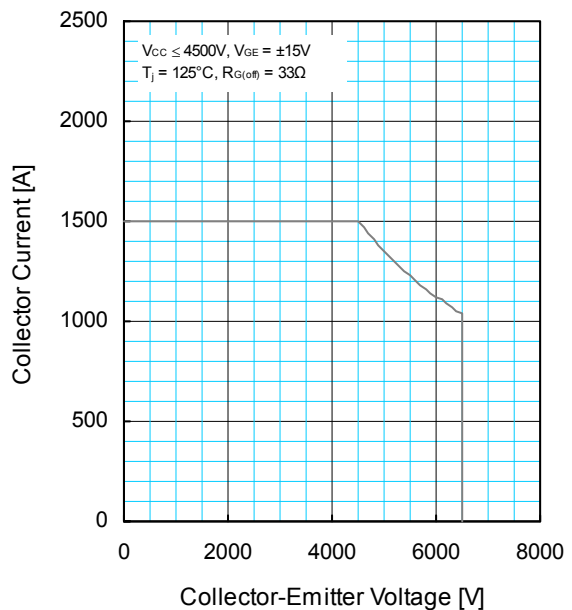
HALF-BRIDGE SWITCHING TIME CHARACTERISTICS (TYPICAL)



FREE-WHEEL DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

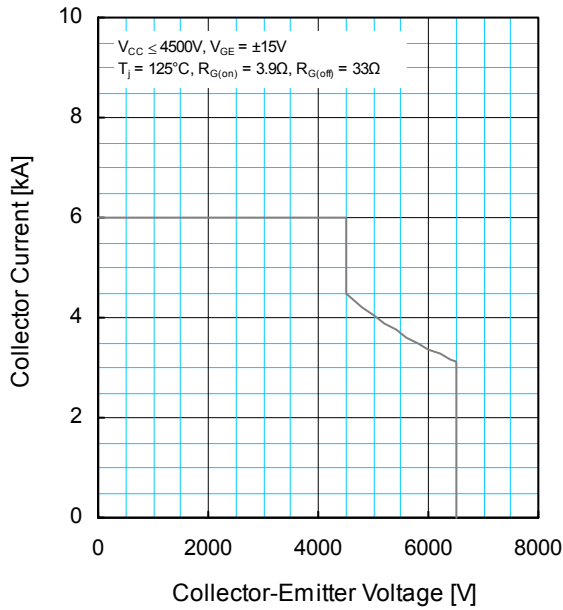


REVERSE BIAS SAFE OPERATING AREA (RBSOA)

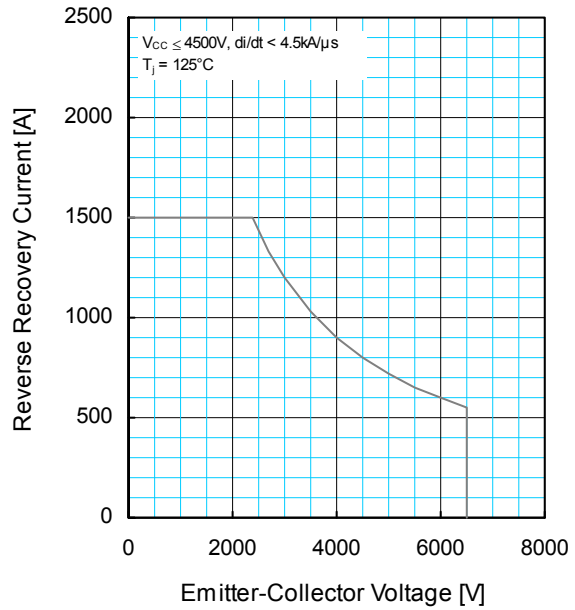


PERFORMANCE CURVES

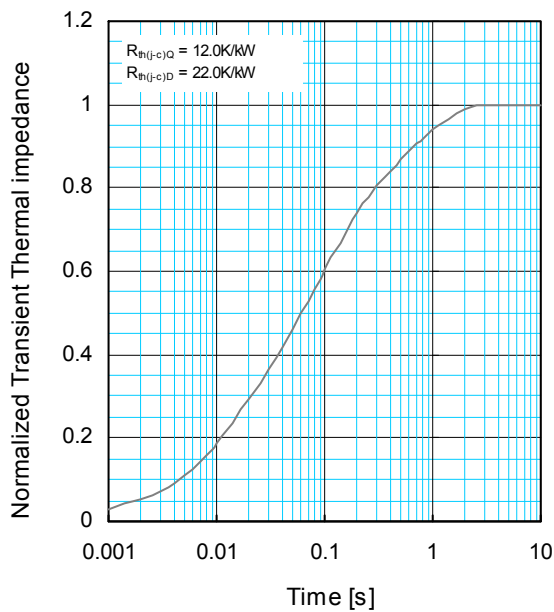
**SHORT CIRCUIT
SAFE OPERATING AREA (SCSOA)**



**FREE-WHEEL DIODE REVERSE RECOVERY
SAFE OPERATING AREA (RRSOA)**



**TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS**



$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i \left\{ 1 - \exp\left(-\frac{t}{\tau_i}\right) \right\}$$

	1	2	3	4
R_i [K/kW] :	0.0055	0.2360	0.4680	0.2905
t_i [sec] :	0.0001	0.0131	0.0878	0.6247

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